TYPE	INTRINSIC STANDOFF RATIO η		INTERBASE RESISTANCE r_{BB}		PEAK-POINT CURRENT I_P	EMITTER REV. CURRENT I_{EB20} @ V_{B2E}		VALLEY-POINT CURRENT I_V	BASE 1 PEAK VOLTAGE V_{OB1}	CASE
	MIN.	MAX.	MIN.	MAX.	MAX.	MAX.		MIN.	MIN.	
			kΩ	kΩ	μA	μA	V	mA	V	
2N2417	0.51	0.62	4.7	6.8	12	2.0	60	8.0	–	
2N2417A	0.51	0.62	4.7	6.8	12	2.0	60	8.0	3.0	
2N2417B	0.51	0.62	4.7	6.8	6.0	0.2	30	8.0	3.0	
2N2418	0.51	0.62	6.2	9.1	12	2.0	60	8.0	–	
2N2418A	0.51	0.62	6.2	9.1	12	2.0	60	8.0	3.0	
2N2418B	0.51	0.62	6.2	9.1	6.0	0.2	30	8.0	3.0	
2N2419	0.56	0.68	4.7	6.8	12	2.0	60	8.0	–	
2N2419A	0.56	0.68	4.7	6.8	12	2.0	60	8.0	3.0	
2N2419B	0.56	0.68	4.7	6.8	6.0	0.2	30	8.0	3.0	
2N2420	0.56	0.68	6.2	9.1	12	2.0	60	8.0	–	
2N2420A	0.56	0.68	6.2	9.1	12	2.0	60	8.0	3.0	
2N2420B	0.56	0.68	6.2	9.1	6.0	0.2	30	8.0	3.0	
2N2421	0.62	0.75	4.7	6.8	12	2.0	60	8.0	–	
2N2421A	0.62	0.75	4.7	6.8	12	2.0	60	8.0	3.0	
2N2421B	0.62	0.75	4.7	6.8	6.0	0.2	30	8.0	3.0	
2N2422	0.62	0.75	6.2	9.1	12	2.0	60	8.0	–	
2N2422A	0.62	0.75	6.2	9.1	12	2.0	60	8.0	3.0	
2N2422B	0.62	0.75	6.2	9.1	6.0	0.2	30	8.0	3.0	
2N2646	0.56	0.75	4.7	9.1	5.0	12	30	4.0	3.0	
2N2647	0.68	0.82	4.7	9.1	2.0	0.2	30	8.0	6.0	
2N2840	0.62*	–	4.7	9.1	10	1.0	30	.20	–	
2N3980	0.68	0.82	4.0	8.0	2.0	0.01	30	1.0	6.0	
2N4851	0.56	0.75	4.7	9.1	2.0	0.1	30	2.0	3.0	
2N4852	0.70	0.85	4.7	9.1	2.0	0.1	30	4.0	5.0	
2N4853	0.70	0.85	4.7	9.1	0.4	0.05	30	6.0	6.0	
2N4947	0.51	0.69	4.0	9.1	2.0	0.01	30	4.0	3.0	
2N4948	0.55	0.82	4.0	12	2.0	0.01	30	2.0	6.0	
2N4949	0.74	0.86	4.0	12	1.0	0.01	30	2.0	3.0	
2N5431	0.72	0.80	6.0	8.5	0.4	0.01	30	2.0	1.0	
MU20	0.50	0.85	4.0	10	5.0	1.0	30	1.0	3.0	
MU2646M	0.56	0.75	4.7	9.1	5.0	12	30	2.0	3.0	

*Typical Value

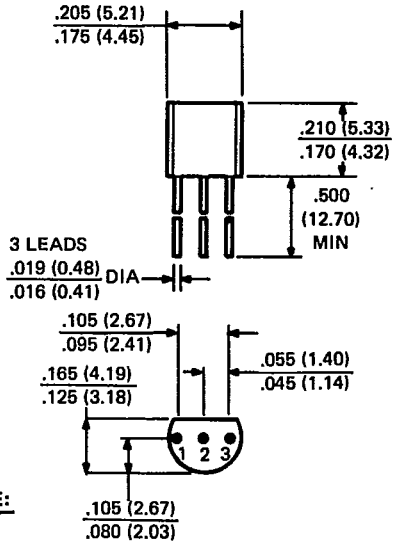
TABLE C — UNIJUNCTION TRANSISTORS — TO-92 CASE

TYPE	INTRINSIC STANDOFF RATIO η		INTERBASE RESISTANCE r_{BB}		PEAK-POINT CURRENT I_P	EMITTER REV. CURRENT I_{EB20} @ V_{B2E}		VALLEY-POINT CURRENT I_V	BASE 1 PEAK VOLTAGE V_{OB1}	CASE
	MIN.	MAX.	MIN.	MAX.	MAX.	MAX.		MIN.	MIN.	
			kΩ	kΩ	μA	μA	V	mA	V	
2N4870	0.56	0.75	4.0	9.1	5.0	1.0	30	2.0	3.0	
2N4871	0.70	0.85	4.0	9.1	5.0	1.0	30	4.0	5.0	
MU10	0.50	0.85	4.0	10	5.0	1.0	30	1.0	3.0	
MU2646	0.56	0.75	4.7	9.1	5.0	12	30	4.0	3.0	
MU4891	0.55	0.82	4.0	9.1	5.0	0.01	30	2.0	3.0	
MU4892	0.51	0.69	4.0	9.1	2.0	0.01	30	2.0	3.0	
MU4893	0.55	0.82	4.0	12	2.0	0.01	30	2.0	6.0	
MU4894	0.74	0.86	4.0	12	1.0	0.01	30	2.0	3.0	

TABLE D — PROGRAMMABLE UNIJUNCTION TRANSISTORS — TO-92 CASE

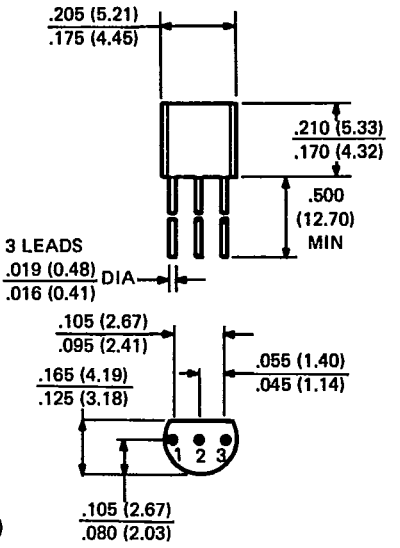
TYPE	MAXIMUM RATINGS		GATE TO ANODE LEAKAGE CURRENT	PEAK CURRENT I_P		VALLEY CURRENT I_V		CASE
	GATE TO ANODE REVERSE VOLTAGE V_{GAR}	DC ANODE CURRENT I_T	I_{GAO} @ 40v	R_G = 10kΩ	R_G = 1.0MΩ	R_G = 10kΩ	R_G = 1.0MΩ	
			MAX.	MAX.	MAX.	MIN.	MAX.	
	V	mA	nA	μA	μA	μA	μA	
2N6027	40	150	10	5.0	2.0	70	50	
2N6028	40	150	10	1.0	0.15	25	25	
A7T6027	40	150	10	5.0	2.0	70	50	
A7T6028	40	150	10	1.0	0.15	25	25	

CASE OUTLINE DRAWINGS



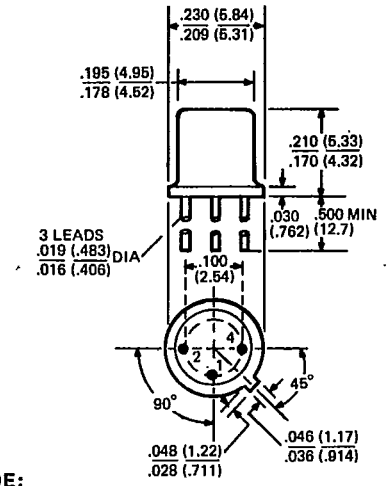
LEAD CODE:
1. BASE 1
2. EMITTER
3. BASE 2

TO-92 (UJT)



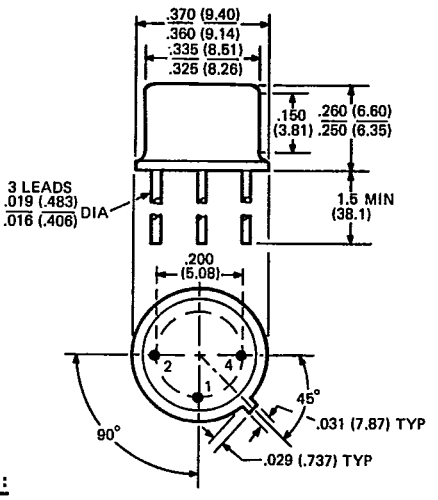
LEAD CODE:
1. ANODE (A)
2. GATE (G)
3. CATHODE (K)

TO-92 (PUT)



LEAD CODE:
1. EMITTER
2. BASE 1
4. BASE 2

TO-18*



LEAD CODE:
1. EMITTER
2. BASE 1
4. BASE 2

TO-5*

DIMENSIONS IN INCHES (MILLIMETERS)

DRAWINGS NOT TO SCALE.

*Conforms to JEDEC outline except for lead configuration.

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Hauppauge, NY 11788
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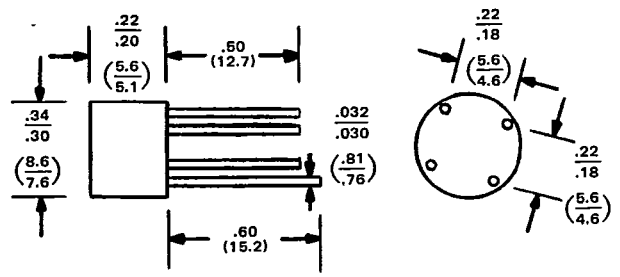
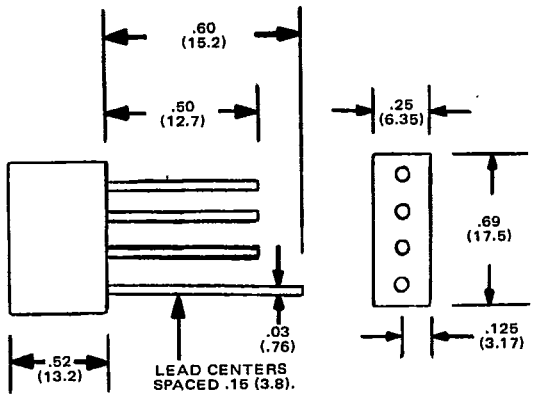
MANUFACTURERS OF DISCRETE SEMICONDUCTORS

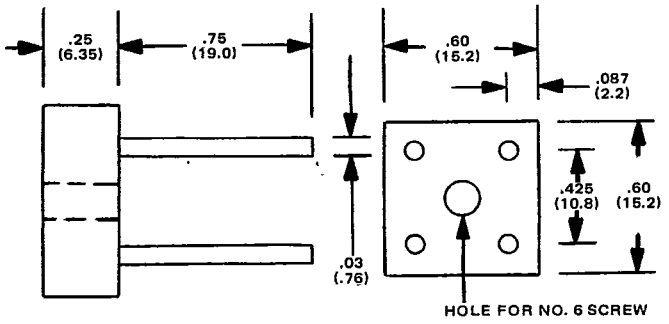
CASE OUTLINE DRAWINGS



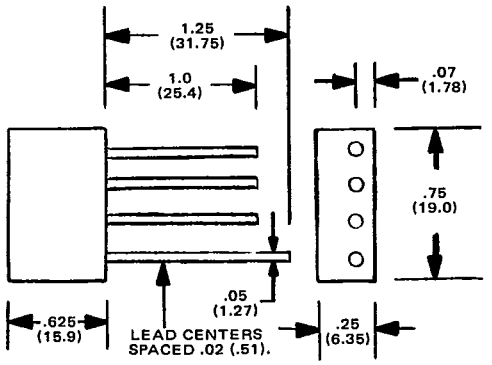
CASE A CBR1 *Series*
CBR2 *Series*



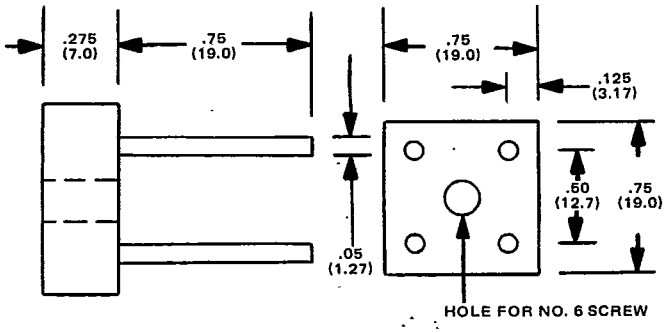
CASE B CBR1-L *Series*
CBR2-L *Series*



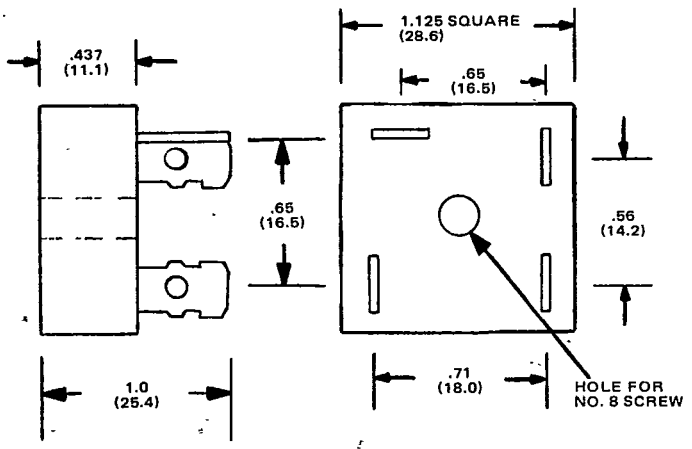
CASE C CBR3-P *Series*



CASE D CBR4-L *Series*



CASE E CBR8 *Series*



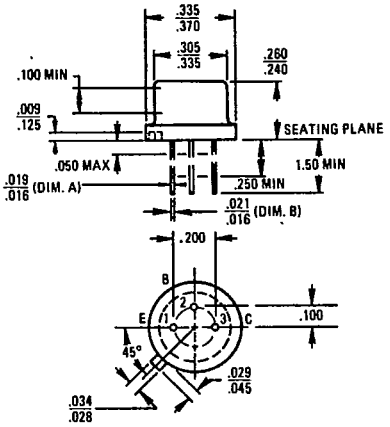
CASE F CBR10 *Series*, CBR25 *Series*
CBR12 *Series*, CBR30 *Series*

All Dimensions in Inches *(Millimeters)*
Drawings Not To Scale

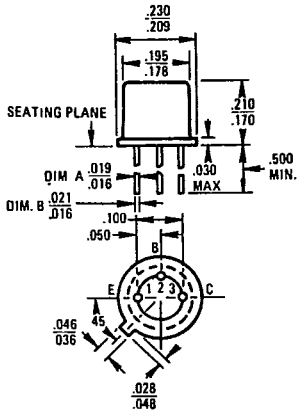
MECHANICAL OUTLINE DRAWINGS

D

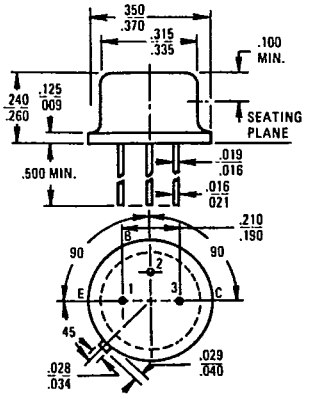
TO-5



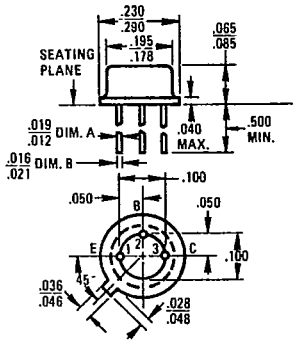
TO-18



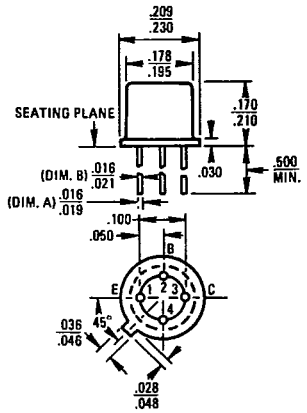
TO-39



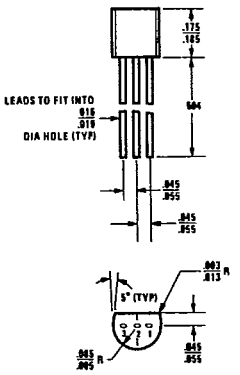
TO-46



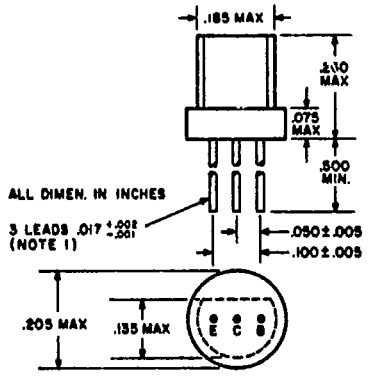
TO-72



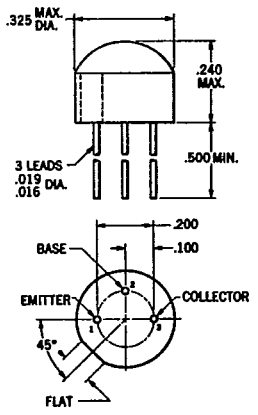
TO-92



TO-98



TO-105



TO-106